



# 1996 IEEE GaAs IC Symposium

INTEGRATED CIRCUITS IN GaAs, InP, and OTHER COMPOUND SEMICONDUCTORS



November 3-6, 1996  
Peabody Hotel, Orlando, FL



Co-Sponsored by the IEEE Electron Devices and Microwave Theory & Techniques Societies



## **1st CALL FOR PAPERS, ABSTRACT DEADLINE: May 10, 1996**

Over the last 18 years, the IEEE GaAs IC Symposium has become the preeminent international forum on developments in integrated circuits made of GaAs, InP, and other compound semiconductors. Coverage embraces all aspects of the technology, from materials issues and device fabrication through IC design and testing, high volume manufacturing and systems applications. High-quality, first-time submissions are sought in the fields of high-speed digital, analog, microwave/millimeter wave, mixed mode, and optoelectronic integrated circuits. Areas of interest include:

High Speed Digital IC's  
Micro/mm Wave IC's  
OEIC's  
Circuit Design  
Device/Circuit Modeling

Circuit Fabrication  
Manufacturing  
Cost Reduction Methods  
IC Testing  
Packaging Technology

Reliability  
Advanced Device Applications  
Commercial Products  
Wireless Applications  
Military Applications

## **SYMPOSIUM HIGHLIGHTS**

Based on past history, it is anticipated that over 70 technical papers will be selected from world-wide submissions for oral presentation and publication in the Symposium Digest. Invited papers and panel sessions on topics of current importance to the GaAs IC technical community will complete the program. For further information on the Symposium content, please contact Phil Wallace, Anadigics Inc., Phone (908) 412-5987, FAX (908) 412-5985, or [pwallace@anadigics.com](mailto:pwallace@anadigics.com).

## **GUIDELINES FOR ABSTRACT SUBMISSION DEADLINE: RECEIPT BY CLOSE OF BUSINESS May 10, 1996**

Authors must submit one-page abstracts of results not previously published or not already accepted by another conference. Additional supporting material (2-page maximum) may also be submitted at the discretion of the authors. Papers will be selected based on the abstract which should concisely and clearly state: (a) The purpose of the work, (b) What specific new results have been obtained, and (c) How much it advances the state of the art or industry. The abstract and supporting material should be typewritten on one side of the paper only, and must include: title, name(s) of the author(s), organization(s) represented, correspondence author's postal and electronic addresses, and phone and FAX number.

**Mail forty (40) copies of the one-page abstract and any supporting material to:**

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**GaAs IC WWW URL:** <http://www.eecs.umich.edu/VLSI/GAASIC>